

WHAT IS CLAIMED IS:

1. A microelectronic component comprising at least one barrier layer formed from WN_x , where x is selected as a value between 0.3 and 0.5.
2. The microelectronic component of claim 1, further comprising a first layer made of a conductive material adjoining at least one side of the barrier layer formed from WN_x .
3. The microelectronic component of claim 2, further comprising a second layer made of a conductive material adjoining the side of the barrier layer formed from WN_x , opposite to the first layer made of a conductive material,
wherein the first layer and of the second layer may be comprised of the same conductive material.
4. The microelectronic component of claim 3, further comprising a layer stack that is constructed from at least the first layer made of a conductive material,
the barrier layer formed from WN_x and the second layer made of a conductive material forming a contact between an interconnect and a structural element of the microelectronic component.
5. The microelectronic component of claim 3, further comprising a layer stack that is constructed from at least the first layer made of a conductive material,
the barrier layer formed from WN_x and the second layer made of a conductive material forming a gate electrode of a transistor.

6. The microelectronic component of claim 3, wherein at least one of the first layer and the second layer is constructed from tungsten.

7. The microelectronic component of claim 3, wherein at least one of the first layer and the second layer being constructed from polysilicon.

8. A method for fabricating a microelectronic component comprising:
forming at least one barrier layer from WN_x ;
providing an area from a first layer of a structural element of the microelectronic component for depositing the barrier layer; and
depositing a second layer on the barrier layer;
wherein the barrier layer is deposited on the area from a nitrogen precursor compound and a tungsten precursor compound, the deposited quantity of the tungsten precursor compound and the deposited quantity of the nitrogen precursor compound selected such that x assumes a value of between 0.3 and 0.5.

9. The method of claim 8, wherein the barrier layer formed from WN_x is deposited by means of a chemical vapor deposition.

10. The method of claim 8, wherein the barrier layer formed from WN_x is deposited by means of a physical vapor deposition.

11. The method of claim 8, wherein the first layer is constructed from a conductive material.

12. The method of claim 8, wherein the second layer deposited on the barrier layer formed from WN_x is constructed from an electrically conductive material.

13. The method of claim 8, wherein the first and second layer is constructed from tungsten.

14. The method of claim 8, wherein at least one of the first and second layer is constructed of polysilicon.

15. The method of claim 14, wherein the polysilicon is doped.